

Amendments to the Claims:

This listing of the claims will replace all prior versions, and listings, of claims in the application:

Claims 1-7 (canceled).

Claim 8 (previously presented): A method comprising:

providing a semiconductor device having at least two metal interconnect layers and a dielectric layer comprising a low dielectric constant material between the metal interconnect layers;

etching the device in aqueous solution of HF and HCl and so that the etching does not stop on the low dielectric constant material and the dielectric layer is etched.

Claim 9 (original): A method as set forth in claim 8 wherein the weight ratio of HF to HCl in the solution ranges from 1:3 to 4:1.

Claim 10 (original): A method as set forth in claim 8 wherein the low dielectric constant material includes -OR groups wherein R is a hydrocarbon derivative.

Claim 11 (original): A method as set forth in claim 8 wherein the low dielectric constant includes methyloxy groups.

Claim 12 (original): A method as set forth in claim 8 wherein the metal interconnect consists essentially of copper.

Claim 13 (original): A method as set forth in claim 8 wherein the metal interconnect comprises aluminum.

Claim 14 (original): A method as set forth in claim 8 wherein the step of etching the device is carried out by dipping the device in a bath of the aqueous solution of HF and HCl.

Claim 15 (original): A method as set forth in claim 8 wherein the low dielectric constant material has a dielectric constant less than 3.8.

Claim 16 (original): A method as set forth in claim 8 wherein the low dielectric constant material comprises fluorosilicate glass.

Claim 17 (original): A method as set forth in claim 9 wherein the aqueous solution includes deionized water and wherein the weight ratio of the deionized water to either HF or HCl ranges from about 20:1 to 6:5.

Claim 18 (original): A method as set forth in claim 8 wherein the low dielectric constant material is hydrophobic.

Claim 19 (original): A method as set forth in claim 8 wherein the low dielectric constant material comprises an organosilicon.

Claim 20 (original): A method as set forth in claim 8 wherein the low dielectric constant material comprises an organic based film.

Claim 21 (cancelled)

Claim 22 (previously presented): A method as set forth in claim 8 wherein the low dielectric constant material includes $\text{Si}(\text{CH}_3)_x\text{O}_{2-x}$.

Claim 23 (canceled).

Claim 24 (previously presented): A method as set forth in claim 8 further comprising analyzing the etched device in a scanning electron microscope.